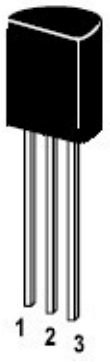
2SC5345 NPN Silicon Epitaxial Planar Transistor

RF amplifier applications.

The transistor is subdivided into three groups, R, O and Y. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Collector Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

Characteristics at T_{amb}=25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at V_{CE}=6V, I_C=1mA	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
Collector Base Breakdown Voltage at I_C=10μA		V_{CBO}	30	-	-	V
Collector Emitter Breakdown Voltage at I_C=5mA		V_{CEO}	20	-	-	V
Emitter Base Breakdown Voltage at I_E=10μA		V_{EBO}	4	-	-	V
Collector Cutoff Current at V_{CB}=30V		I_{CBO}	-	-	0.5	μA
Emitter Cutoff Current at V_{EB}=4V		I_{EBO}	-	-	0.5	μA
Collector Emitter Saturation Voltage at I_C=10mA, I_B=1mA		$V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at V_{CE}=6V, I_E=-1mA		f_T	-	550	-	MHz
Collector Output Capacitance at V_{CB}=6V, f=1MHz		C_{OB}	-	1.4	-	pF